



Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



June 2013

FJP5555

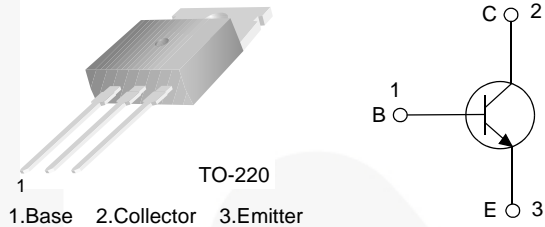
NPN Silicon Transistor

Features

- Fast Speed Switching
- Wide Safe Operating Area
- High Voltage Capability

Application

- Electronic Ballast
- Switch Mode Power Supplies



Ordering Information

Part Number	Marking	Package	Packing Method
FJP5555TU	J5555	TO-220	Rail

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Units
BV_{CBO}	Collector-Base Voltage	1050	V
BV_{CEO}	Collector-Emitter Voltage	400	V
BV_{EBO}	Emitter-Base Voltage	14	V
I_C	Collector Current (DC)	5	A
I_{CP}	Collector Current (Pulse)	10	A
I_B	Base Current (DC)	2	A
I_{BP}	Base Current (Pulse)	4	A
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 55 to +150	$^\circ\text{C}$

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Units	
P_D	Total Device Dissipation	$T_A = 25^\circ\text{C}$	1.38	W
		$T_C = 25^\circ\text{C}$	75	W
$R_{\theta ja}^{(1)}$	Thermal Resistance, Junction to Ambient	90	$^\circ\text{C}/\text{W}$	
$R_{\theta jc}^{(2)}$	Thermal Resistance, Junction to Case	1.66	$^\circ\text{C}/\text{W}$	

Notes:

1. $R_{\theta ja}$ test board and fixture under natural convection, JESD51-10 recommended thermal test board.
2. $R_{\theta jc}$ test fixture under infinite cooling condition.

Electrical Characteristics⁽³⁾Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Voltage	$I_C = 500 \mu\text{A}, I_E = 0$	1050			V
BV_{CEO}	Collector-Emitter Voltage	$I_C = 5 \text{ mA}, I_B = 0$	400			V
BV_{EBO}	Emitter-Base Voltage	$I_E = 500 \mu\text{A}, I_C = 0$	14			V
h_{FE}	DC Current Gain	$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}$	10			
		$V_{CE} = 3 \text{ V}, I_C = 0.8 \text{ A}$	20		40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1 \text{ A}, I_B = 0.2 \text{ A}$			0.5	V
		$I_C = 3.5 \text{ A}, I_B = 1.0 \text{ A}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 3.5 \text{ A}, I_B = 1.0 \text{ A}$			1.2	V
C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$		45		pF
t_{ON}	Turn-On Time	$V_{CC} = 125 \text{ V}, I_C = 0.5 \text{ A},$ $I_{B1} = 45 \text{ mA}, I_{B2} = 0.5 \text{ A},$ $R_L = 250 \Omega$			1.0	μs
t_{STG}	Storage Time				1.2	μs
t_F	Fall Time				0.3	μs
t_{ON}	Turn-On Time	$V_{CC} = 250 \text{ V}, I_C = 2.5 \text{ A},$ $I_{B1} = 0.5 \text{ A}, I_{B2} = 1.0 \text{ A},$ $R_L = 100 \Omega$			2.0	μs
t_{STG}	Storage Time				2.5	μs
t_F	Fall Time				0.3	μs
EAS	Avalanche Energy	$L = 2 \text{ mH}$	6			mJ

Note:3. Pulse test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

Typical Performance Characteristics

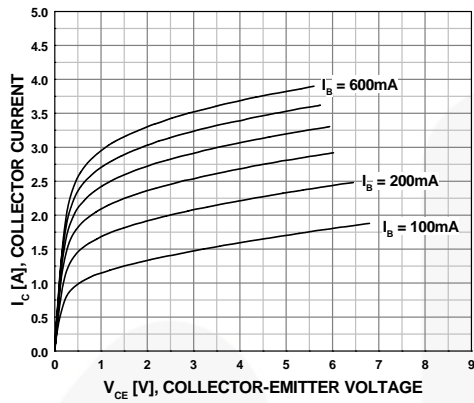


Figure 1. Static Characteristics

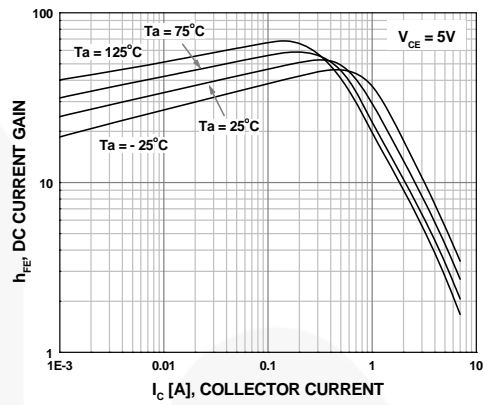


Figure 2. DC Current Gain

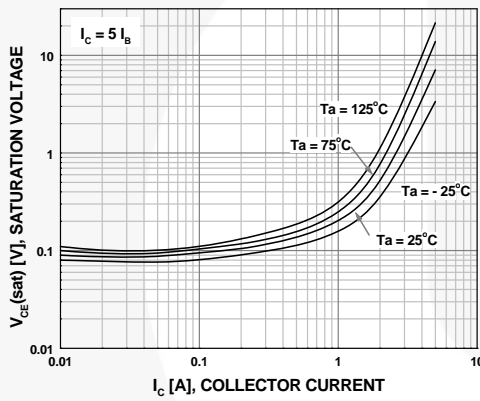


Figure 3. Saturation Voltage

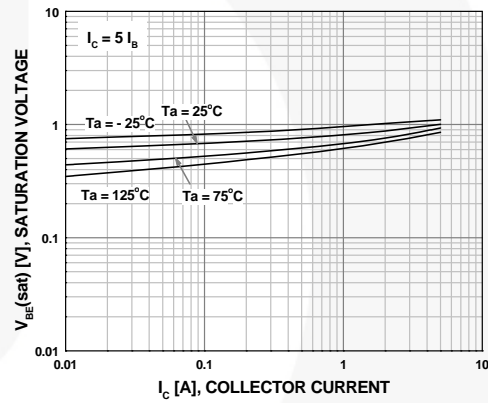


Figure 4. Saturation Voltage

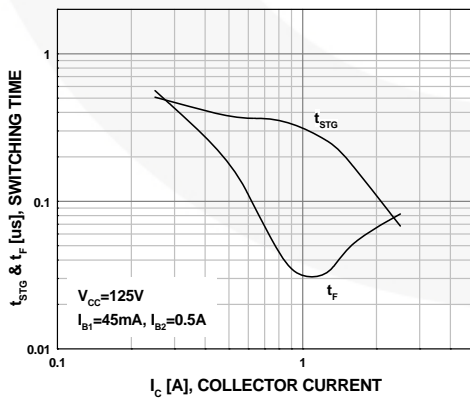


Figure 5. Resistive Load Switching

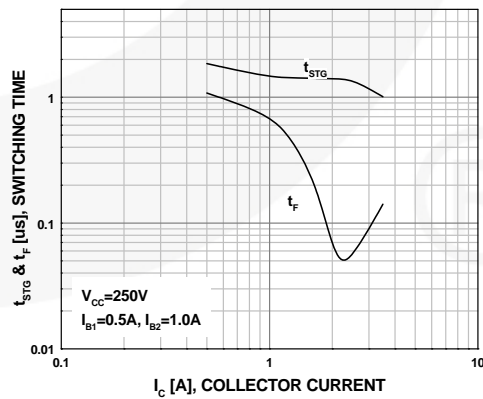


Figure 6. Resistive Load Switching

Typical Performance Characteristics (Continued)

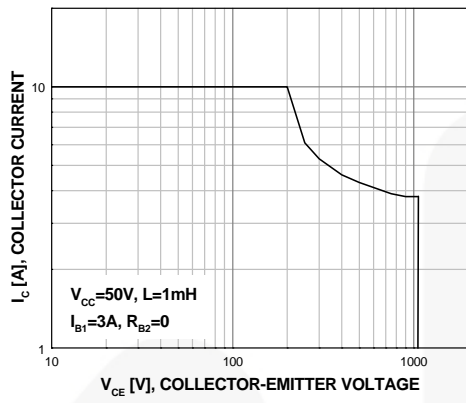


Figure 7. Reverse Biased Safe Operating Area

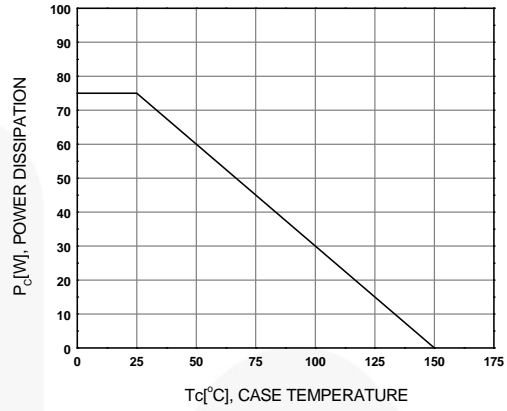


Figure 8. Power Derating

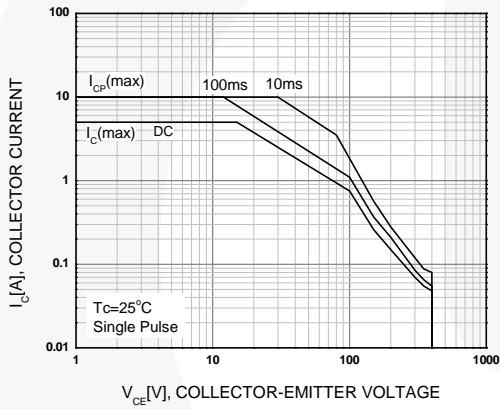
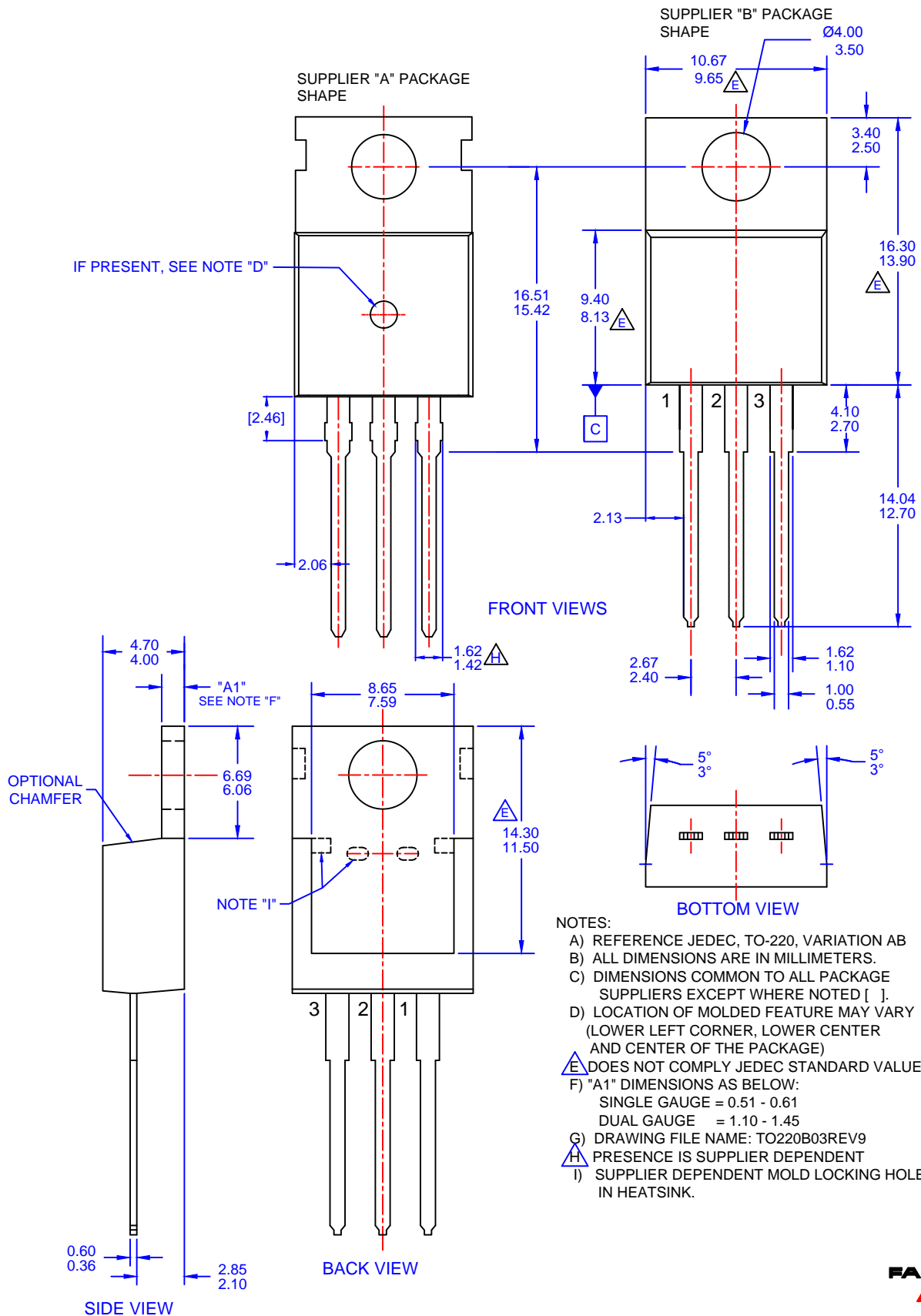


Figure 9. Forward Biased Safe Operating Area



- NOTES:**
- A) REFERENCE JEDEC, TO-220, VARIATION AB
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
 - D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
 - E) DOES NOT COMPLY JEDEC STANDARD VALUE.
 - F) "A1" DIMENSIONS AS BELOW:
 SINGLE GAUGE = 0.51 - 0.61
 DUAL GAUGE = 1.10 - 1.45
 - G) DRAWING FILE NAME: TO220B03REV9
 - H) PRESENCE IS SUPPLIER DEPENDENT
 - I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local
Sales Representative